



**High Speed CMOS
Bus Interface
8-bit Latches**

QS54/74FCT573T

QS54/74FCT2573T

FEATURES/BENEFITS

- Pin and function compatible to the 74F573, 74FCT573 and 74FCT573T
- CMOS power levels: <7.5 mW static
- Available in DIP, ZIP, SOIC, QSOP, LCC
- Undershoot clamp diodes on all inputs
- TTL-compatible input and output levels
- Ground bounce controlled outputs
- Reduced output swing of 0-3.5V
- Military product compliant to MIL-STD-883

FCT-T 573T

- JEDEC-FCT spec compatible
- Fastest CMOS logic family available
- Std, A, and C speed grades with 4.7 ns tPD for C
- I_{OL} = 48 mA Com., 32 mA Mil.

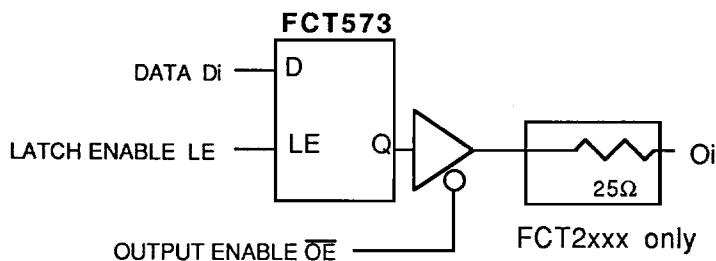
FCT-T 2573T

- Built-in 25Ω series resistor outputs reduce reflection and other system noise
- Std, thru C speed grades with 4.7 ns tPD for C
- I_{OL} = 12mA Com.

DESCRIPTION

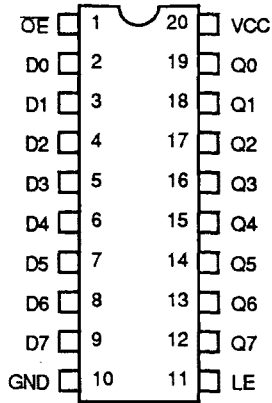
The QSFCT573T and QSFCT2573T are 8-bit high-speed CMOS TTL-compatible buffered latches with three-state outputs that are ideal for driving high capacitance loads such as memory and address buses. The 2573 devices are 25Ω resistor output versions useful for driving transmission lines and reducing system noise. The 2573 series parts can replace the 573 series to reduce noise in an existing design. All inputs have clamp diodes for undershoot noise suppression. All outputs have ground bounce suppression (see QSI Application Note AN-001), and outputs will not load an active bus when V_{CC} is removed from the device.

FUNCTIONAL BLOCK DIAGRAM

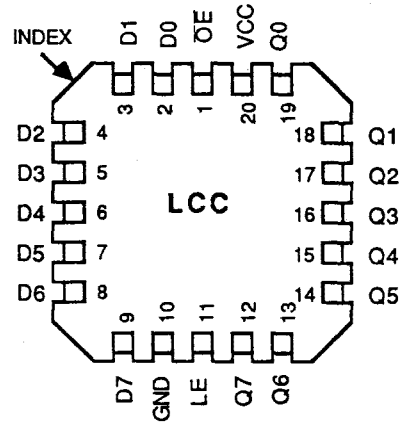
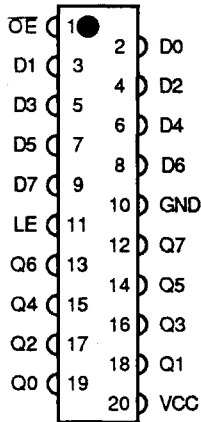


PINOCTS

PDIP, SOIC, QSOP



ZIP



ALL PINS TOP VIEW

PIN DESCRIPTIONS

Name	I/O	Description
Di	I	Data Inputs
O _i	O	Data Outputs
LE	I	Latch Enable
O _E	I	Output Enable

FUNCTION TABLE

Inputs			Internal Q Value	Outputs	Function
O _E	LE	Di		O _i	
H	X	X	X	Z	Disable Outputs
L	L	X	L	L	Enable Outputs
L	L	X	H	H	
X	H	L	L	L	Pass Input Data
X	H	H	H	H	
L	L	X	Q	Q	Hold Prior Data

ABSOLUTE MAXIMUM RATINGS

Supply Voltage to Ground..... -0.5V to +7.0V
 DC Output Voltage V_O -0.5V to 7.0V
 DC Input Voltage V_I -0.5V to 7.0V
 AC Input Voltage (for a pulse width ≤ 20 ns)..... -3.0V
 DC Input Diode Current with $V_I < 0$ -20 mA
 DC Output Diode Current with $V_O < 0$ -50 mA
 DC Output Current Max. sink current/pin..... 120 mA
 Maximum Power Dissipation..... 0.5 watts
 T_{STG} Storage Temperature..... -65° to +165°C

CAPACITANCE

TA = 25 °C, f = 1 MHz, Vin = 0V, Vout = 0 V

Pins	SOIC	QSOP	PDIP,LCC	ZIP	Unit
1-9, 11	4	4	5	7	pF
12-19	6	6	7	9	pF
-----	8	8	9	10	pF

Note: Capacitance is characterized but not tested

QSFCT573T, 2573T

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Commercial $T_A=0^{\circ}\text{C}$ to 70°C , $V_{CC}=5.0\text{V}\pm 5\%$

Military $T_A=-55^{\circ}\text{C}$ to 125°C , $V_{CC}=5.0\text{V}\pm 10\%$

Symbol	Parameter	Test Conditions		Min	Typ (1)	Max	Unit
Vih	Input High Voltage	Logic HIGH for All Inputs		2.0	-	-	Volts
Vil	Input LOW Voltage	Logic LOW for All Inputs		-	-	0.8	
ΔV_t	Input Hysterisis	$V_{th} - V_{tl}$ for All Inputs		-	0.2	-	
$ i_{ih} $ $ i_{il} $	Input Current Input HIGH or LOW	$V_{CC} = \text{MAX}$	$0 \leq V_{in} < V_{CC}$	-	-	5	μA
$ i_{oz} $	Off State Output Current (Hi-Z)	$V_{CC} = \text{MAX}, 0 \leq V_{in} \leq V_{CC}$		-	-	5	
Ios	Short Circuit Current FCTXXX	$V_{CC} = \text{MAX}, V_o = \text{GND} (2,3)$		-60	-	-225	mA
Ior	Current Drive FCT2XXX	$V_{CC} = \text{Min}, V_o = 2.0\text{V} (3)$		50	-	-	mA
Vic	Input Clamp Voltage	$V_{CC} = \text{MIN}, I_{in} = 18 \text{ mA} (3)$		-	-0.7	-1.2	Volts
Voh	Output HIGH Voltage FCTXXX & FCT2XXX	$V_{CC} = \text{MIN}$	loh = 12 mA (MIL)	2.4	-	-	Volts
			loh = 15 mA (COM)	2.4	-	-	
Vol	Output LOW Voltage FCTXXX	$V_{CC} = \text{MIN}$	lol = 32 mA (MIL)	-	-	0.50	
			lol = 48 mA (COM)	-	-	0.50	
	Output LOW Voltage FCT2XXX (25 Ω)	$V_{CC} = \text{MIN}$	lol = 12 mA (MIL)	-	-	0.50	
			lol = 12 mA (COM)	-	-	0.50	
Rout	Output Resistance FCT2XXX (25 Ω)	$V_{CC} = \text{MIN}$	lol = 12 mA (MIL)	-	25	-	Ω
			lol = 12 mA (COM)	20	28	40	

Notes:

1. Typical values indicate $V_{CC}=5.0\text{V}$ and $T_A=25^{\circ}\text{C}$.
2. Not more than one output should be shorted and the duration is ≤ 1 second.
3. These parameters are guaranteed by design but not tested.

POWER SUPPLY CHARACTERISTICS

Symbol	Parameter	Test Conditions (1)	Min	Max	Unit
I _{cc}	Quiescent Power Supply Current	V _{cc} = MAX, freq = 0 0V ≤ V _{in} ≤ 0.2V or V _{cc} - 0.2V ≤ V _{in} ≤ V _{cc}	-	1.5	mA
ΔI _{cc}	Supply Current per Input @ TTL HIGH	V _{cc} = MAX, V _{in} = 3.4 V, freq = 0 (2)	-	2.0	
Q _{ccd}	Supply Current per input per mHz	V _{cc} = MAX, Outputs open and enabled One bit toggling @ 50% duty cycle Other inputs at GND or V _{cc} (3,4)	-	0.25	mA/ MHz

1. For conditions shown as MIN or MAX use the appropriate values specified under DC specifications.
2. Per TTL driven input (V_i=3.4V)
3. For flipflops Q_{ccd} is measured by switching one of the data in pins so that the output changes every clock cycle. This is a measurement of device power consumption only and does not include power to drive load capacitance or tester capacitance. This parameter is guaranteed by design but not tested.
4. I_c can be computed using the above parameters as explained in the Technical Overview section.

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SWITCHING CHARACTERISTICS OVER OPERATING RANGE

Commercial $T_A=0^{\circ}\text{C}$ to 70°C , $V_{CC}=5.0\text{V}\pm 5\%$ Military $T_A=-55^{\circ}\text{C}$ to 125°C , $V_{CC}=5.0\text{V}\pm 10\%$
 Load = 50 pF, Rload = 500 Ω unless otherwise noted

Symbol	Description	Notes	573 2573		573A 2573A		573C 2573C		Unit	
			Min	Max	Min	Max	Min	Max		
tPHL tPLH	Propagation Delay Data to Oi, 573	COM	1	1.5	8	1.5	5.2	1.5	4.2	ns
		MIL	1	2	8.5	1.5	5.6			
	Propagation Delay Data to Oi, 2573	COM	1	1.5	8	1.5	5.2	1.5	4.2	
		MIL	1	2	8.5	1.5	5.6			
tPHLE tPLHE	Propagation Delay LE to Oi, 573	COM	1	2	13	2	8.5	2	5.5	
		MIL	1	2	14	2	9.8			
	Propagation Delay LE to Oi, 2573	COM	1	2	13	2	8.5	2	5.5	
		MIL	1	2	14	2	9.8			
tPZH tPZL	Output Enable Time $\overline{\text{OE}}$ to Yi, 573	COM	1	1.5	11	1.5	6.5	1.5	5.5	
		MIL	1	1.5	12.5	1.5	7.5			
	Output Enable Time $\overline{\text{OE}}$ to Yi, 2573	COM	1	1.5	11	1.5	6.5	1.5	6.5	
		MIL	1	1.5	12.5	1.5	7.5			
tPHZ tPLZ	Output Disable Time $\overline{\text{OE}}$ to Yi	COM	2	1.5	7	1.5	5.5	1.5	5.0	
		MIL	2	1.5	8.5	1.5	6.5			
tS	Data Setup Time Di to LE hi to low	COM		2		2		2		
		MIL		2		2				
tH	Data Hold Time Di to LE hi to low	COM		1.5		1.5		1.5		
		MIL		1.5		1.5				
tW	LE Pulse Width HIGH or LOW	COM	2	6		5		4		
		MIL	2	6		6				

Notes:

- 1) Minimums guaranteed but not tested.
- 2) This parameter is guaranteed by design but not tested.
- 3) See Test Circuit and Waveforms.